

IN THE SPECIFICATION

Please amend the paragraph at page 9, lines 3-24 to read to read as follows:

Fig.4 is a [plan] cross sectional view taken on line IV-IV in Fig.3, showing that the semiconductor chip 1 is assembled with flip chip architecture by the bumps 6a, ····, 6g, ···· on the first main surface of the module substrate 2. In the high frequency module according to the first embodiment, gallium arsenide (GaAs) is used for the semiconductor chip 1. The GaAs chip 1 is polished thinly to about 150 μ m. Further, in the first embodiment, a metallic film composed of single metal such as gold-germanium alloy (Au-Ge), titanium (Ti), gold (Au), nickel (Ni), palladium (Pd), platinum (Pt), molybdenum (Mo), tungsten (W), aluminum (Al) or a laminated structure by combination of more than two of these metals is formed on bottom surface of the semiconductor chip 1 as the back electrode 11. On the top surface of the semiconductor chip 1 opposing to the back electrode 11, bonding pads 7a, ····, 7g, ···· composed of metallic film such as Al, Au and aluminum alloy (Al-Si, Al-Cu-Si) are formed. On each of these bonding pads 7a, ····, 7g, ····, bumps 6a, ····, 6g, ···· are disposed to be mounted on the module substrate 2 by the flip chip configuration. A stud bumps made of gold (Au) are used for the bumps 6a, ····, 6g, ····. Besides gold bump, silver (Ag) bump, copper (Cu) bump, nickel-gold (Ni-Au) bump and nickel-gold-indium (Ni-Au-In) bump and another material can be used.